

FAN73832 Half-Bridge Gate-Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- Typically 350mA/650mA Sourcing/Sinking Current Driving Capability for Both Channels
- Extended Allowable Negative V_S Swing to -9.8V for Signal Propagation at V_{DD}=V_{BS}=15V
- High-Side Output in Phase of IN Signal
- Built-in UVLO Functions for Both Channels
- Built-in Common-Mode dv/dt Noise Canceling Circuit
- Internal 400ns Minimum Dead-Time at R_{DT}=20KΩ
- Programmable Turn-on Delay-Time Control (Dead-Time)

Applications

- SMPS
- Motor Drive Inverter
- Fluorescent Lamp Ballast
- HID Ballast

Description

The FAN73832 is a half-bridge, gate-drive IC with shutdown and programmable dead-time control functions for driving MOSFETs and IGBTs, operating up to +600V.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-side driver under high dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to $V_{\rm S}$ =-9.8V (typical) for $V_{\rm BS}$ =15V.

The UVLO circuits for both channels prevent malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage.

Output drivers typically source/sink 350mA/650mA, respectively, which is suitable for all kinds of half- and full-bridge inverters.





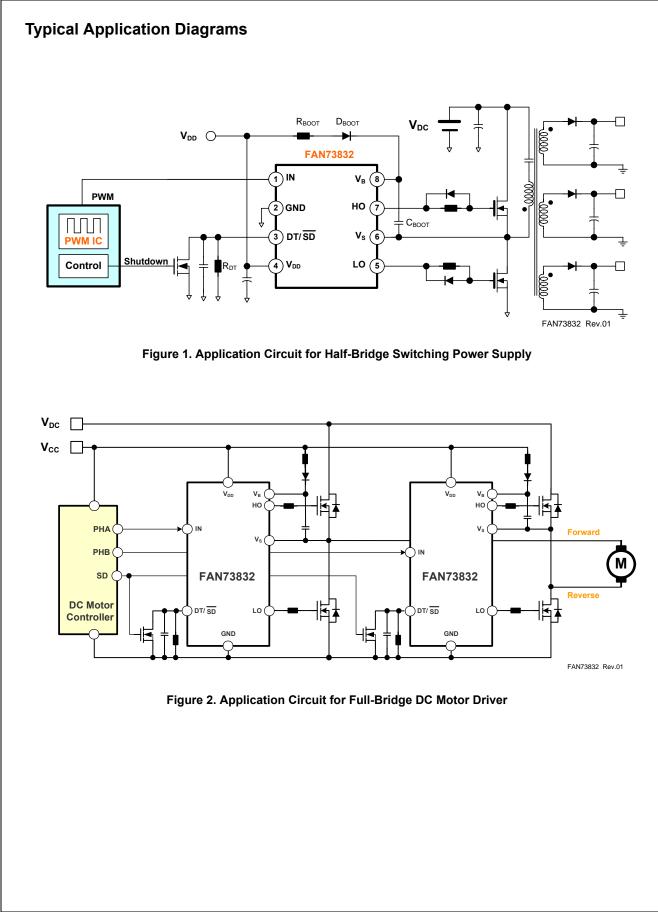
Ordering Information

Part Number	Package	Pb-Free	Operating Temperature Range	Packing Method
FAN73832M ⁽¹⁾	8-SOP			Tube
FAN73832MX ⁽¹⁾	0-30F	Yes	-40°C ~ 125°C	Tape & Reel
FAN73832N	8-DIP			Tube

Note:

1. These devices passed wave soldering test by JESD22A-111.

February 2007





V_B

но

Vs

 \mathbf{V}_{DD}

LO

GND

8

7

6

4

5

2

FAN73832 Rev:00

UVLO

RR

DELAY

s q

NOISE CANCELLER

UVLO

DRIVER

DRIVER

Internal Block Diagram

SCHMITT TRIGGER INPUT

DEAD - TIME CONTROL

Ì

R.

3

IN (1

DT/SD

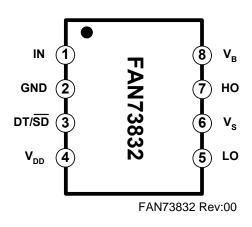
Figure 3. Functional Block Diagram of FAN73832

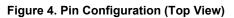
HS(ON/OFF)

LS(ON/OFF)

FAN73832 Half-Bridge Gate-Drive IC

Pin Assignments





Pin Definitions

Pin #	Name	Description	
1	IN	Logic Input	
2	GND	Ground	
3	DT/SD	Dead-Time Control with External Resistor and Shutdown Function	
4	V _{DD}	ow-Side Supply Voltage	
5	LO	ow-Side Driver Output	
6	Vs	gh-Side Floating Supply Return	
7	HO	High-Side Driver Output	
8	V _B	High-Side Floating Supply	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}C$ unless otherwise specified.

Symbol	Parameter		Min.	Max.	Unit
V _S	High-side offset voltage		V _B -25	V _B +0.3	V
V _B	High-side floating supply voltage		-0.3	625	V
V _{HO}	High-side floating output voltage HO		V _S -0.3	V _B +0.3	V
V _{DD}	Low-side and logic-fixed supply voltage		-0.3	25	V
V _{LO}	Low-side output voltage LO		-0.3	V _{DD} +0.3	V
V _{IN}	Logic input voltage (IN)		-0.3	V _{DD} +0.3	V
V _{DT/SD}	Dead-time and shutdown control voltage		-0.3	5.0	V
GND	Logic ground		V _{DD} -25	V _{DD} +0.3	V
dV _S /dt	Allowable offset voltage slew rate			50	V/ns
P _D ⁽²⁾⁽³⁾⁽⁴⁾	Dower dissipation	8-SOP		0.625	W
PD	Power dissipation	8-DIP		1.25	
0	Thermal registered, junction to embient	8-SOP		200	°C/W
θ_{JA}	Thermal resistance, junction-to-ambient 8-DIP			100	-0/00
TJ	Junction temperature			150	°C
T _{STG}	Storage temperature			150	°C

Notes:

- 2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- 3. Refer to the following standards:

JESD51-2: Integral circuits thermal test method environmental conditions - Natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages

4. Do not exceed P_D under any circumstances.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Condition	Min.	Max.	Unit
VB	High-side floating supply voltage		V _S +15	V _S +20	V
V _S	High-side floating supply offset voltage		6-V _{DD}	600	V
V _{DD}	Low-side supply voltage		15	20	V
V _{HO}	High-side (HO) output voltage		Vs	VB	V
V _{LO}	Low-side (LO) output voltage		GND	V _{DD}	V
V _{IN}	Logic input voltage (IN)		GND	V _{DD}	V
T _A	Ambient temperature		-40	125	°C

Electrical Characteristics

 V_{BIAS} (V_{DD} , V_{BS})=15.0V, R_{DT} =20K Ω , T_A =25°C, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to GND. The V_O and I_O parameters are referenced to V_S and COM and are applicable to the respective outputs HO and LO.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
SUPPLY C	URRENT SECTION				1	
I _{QBS}	Quiescent V _{BS} supply current	V _{IN} =0V or 5V		35	90	
I _{QDD}	Quiescent V _{DD} supply current	V_{IN} =0V or 5V, R _{DT} =20K Ω		300	450	
I _{SD} ⁽⁵⁾	Shutdown supply current	DT/SD=GND		650	900	
I _{PBS}	Operating V _{BS} supply current	f _{IN} =20kHz, rms value		400	700	μA
I _{PDD}	Operating V _{DD} supply current	f _{IN} =20kHz, rms value		650	850	
I _{LK}	Offset supply leakage current	V _B =V _S =600V			10	
POWER SI	JPPLY SECTION					
V _{DDUV+} V _{BSUV+}	V _{DD} and V _{BS} supply under-voltage positive going threshold		10.7	11.6	12.5	V
V _{DDUV-} V _{BSUV-}	V _{DD} and V _{BS} supply under-voltage negative going threshold		10.0	10.8	11.6	V
V _{DDUVH} V _{BSUVH}	V _{DD} supply under-voltage lockout hysteresis			0.8		V
DEAD-TIM	E CONTROL SECTION	·			•	
R _{DTINT}	Internal dead-time setting resistance			20		KΩ
V _{DT}	Normal voltage at DT	R _{DT} =20KΩ		3.0		V
GATE DRIV	/ER OUTPUT SECTION					
V _{OH}	High-level output voltage, V _{BIAS} -V _O	I _O =20mA			1.0	V
V _{OL}	Low-level output voltage, V _O				0.6	V
I _{O+}	Output high short-circuit pulse current	V_{O} =0V, V_{IN} =5V with PW<10µs	250	350		mA
I _{O-}	Output low short-circuit pulsed current	V_{O} =15V, V_{IN} =0V with PW<10µs	500	650		mA
VS	Allowable negative V _S pin voltage for IN signal propagation to HO			-9.8	-7.0	V
LOGIC INP	UT SECTION (INPUT and SHUTDOWN)			•	
V _{IH}	Logic "1" input voltage		2.9			V
V _{IL}	Logic "0" input voltage				1.2	V
I _{IN+}	Logic "1" input bias current	V _{IN} =5V		50	100	μA
I _{IN-}	Logic "0" input bias current	V _{IN} =0V			2.0	μA
SD+	Shutdown "1" input voltage				1.2	V
SD-	Shutdown "0" input voltage		2.9			V
R _{PD}	Input pull-down resistance			100		KΩ

Note:

5. This parameter guaranteed by design.

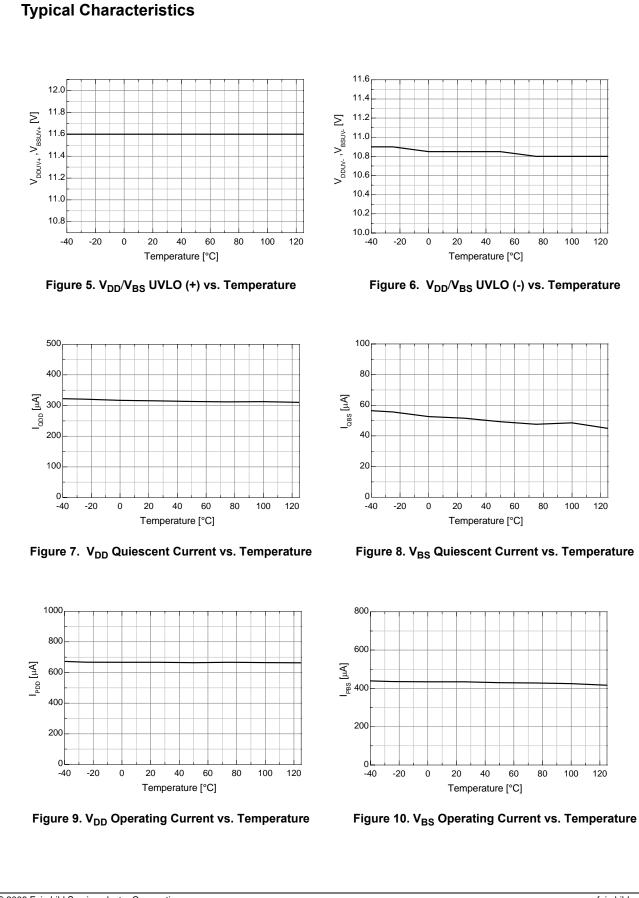
Dynamic Electrical Characteristics

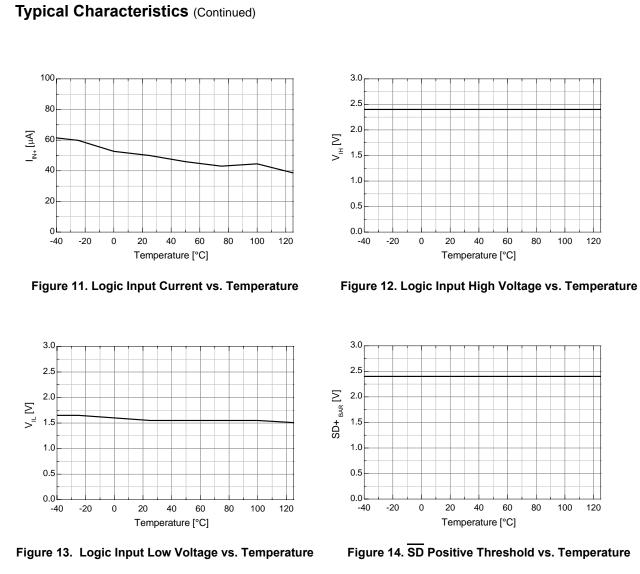
 $V_{BIAS} (V_{DD}, V_{BS}) = 15.0V, V_{S} = GND, C_{L} = 1000 pF, R_{DT} = 20 K\Omega \text{ and } T_{A} = 25^{\circ}C, \text{ unless otherwise specified.}$

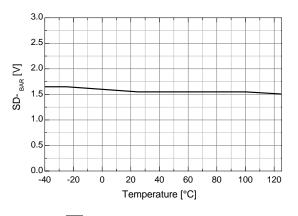
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t _{ON}	Turn-on propagation delay	V_{S} =0V, R_{DT} =20K Ω		580	730	
t _{OFF}	Turn-off propagation delay	V_{S} =0V or 600V ⁽⁵⁾ , R _{DT} =20K Ω		180	230	
t _R	Turn-on rise time	C _L =1000pF		50	100	ns
t _F	Turn-off fall time	C _L =1000pF		30	80	
t _{SD} ⁽⁵⁾	Shutdown propagation delay			100	180	
DT1, DT2	Dead-time LO OFF to HO ON & HO	R _{DT} =20KΩ	300	400	500	ns
011, 012	OFF to LO ON	R _{DT} = 200KΩ	1.20	1.68	2.30	μs
DMT		R _{DT} = 20KΩ		0	60	200
וויוש	Dead-time matching	R _{DT} =200KΩ		0	150	ns

Note:

5. These parameters guaranteed by design.









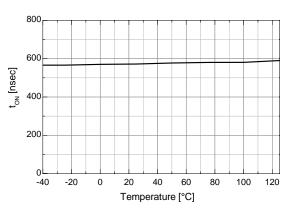
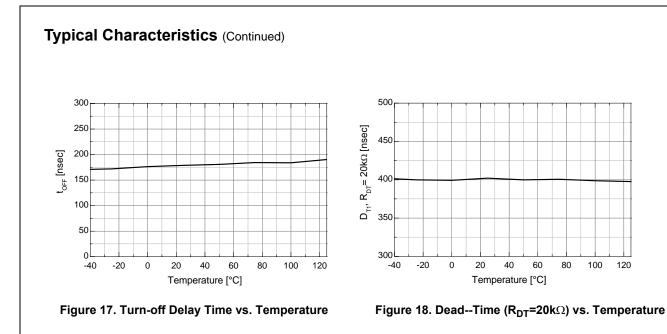


Figure 16. Turn-on Delay Time vs. Temperature

FAN73832 Half-Bridge Gate-Drive IC



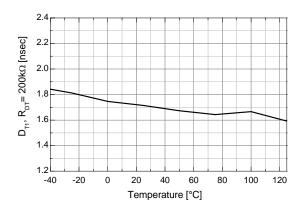


Figure 19. Dead Time (R_{DT}=200k Ω) vs. Temperature

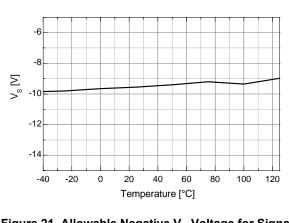


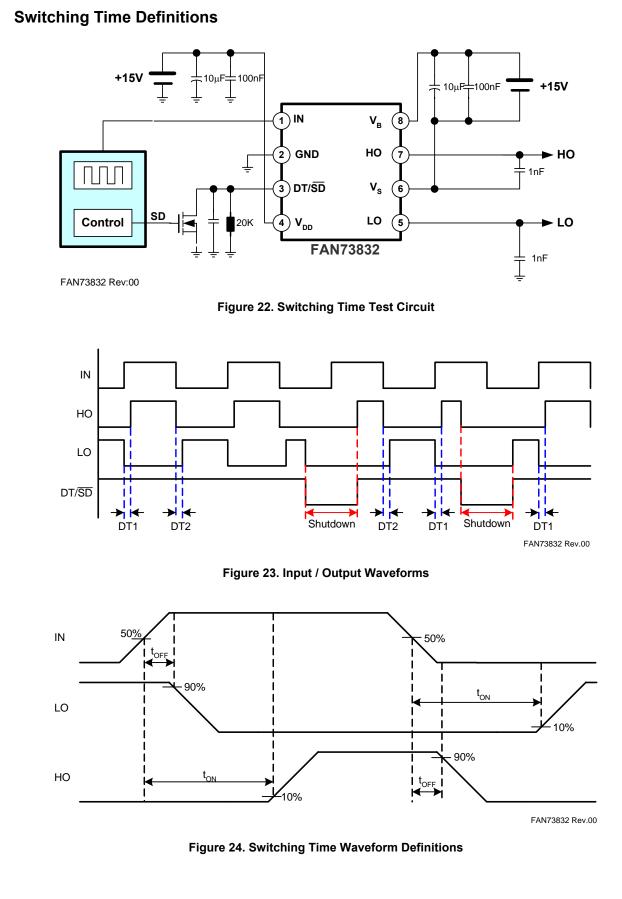
Figure 21. Allowable Negative V_S Voltage for Signal Propagation to High Side vs. Temperature

2.0 1.6 Deadtime [µS] 1.2 0.8 0.4 0.0 20 40 60 80 100 120 140 160 180 200 RDT [kohm]

Figure 20. R_{DT} vs. Dead-Time

FAN73832 Half-Bridge Gate-Drive IC





50% DT/SD 90% HO or LO ۱_{SD} FAN73832 Rev.00 Figure 25. Shutdown Waveform Definition 90% 10% DT1 DT2 90% MDT= DT1 - DT2 10% FAN73832 Rev.00 Figure 26. Dead-Time Control Waveform Definition

HO

LO

Typical Application Information

1. Normal Operating Consideration

The FAN73832 is a single PWM input, half-bridge, gatedrive IC with programmable dead-time and shutdown functions.

The dead-time is set with a resistor (R_{DT}) at the DT/SD pin. The wide dead-time programming range provides the flexibility to optimize drive signal timing for a selection of switching devices (MOSFET or IGBT) and applications.

The turn-on time delay circuitry (Dead-Time) accommodates resistor values from $20k\Omega$ to $200k\Omega$ with a dead-time proportional to the R_{DT} resistance.

If the DT/SD pin voltage decreases below 1.2V in the normal operation, the IC enters shutdown mode.

The external dead-time setting resistor (R_{DT}) is at least above 20K Ω for normal operation in typical applications.

2. Under-Voltage Lockout (UVLO)

The FAN73832 has an under-voltage lockout (UVLO) protection circuit for high- and low-side channels to prevent malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage. The UVLO circuitry monitors the supply voltage (V_{DD}) and bootstrap capacitor voltage (V_{BS}) antepenult.

3. Layout Consideration

For optimum performance of the high- and low-side gate drivers, considerations must be taken during printed circuit board (PCB) layout.

3.1 Supply Capacitors

If the output stages are able to quickly turn-on a switching device with a high value of current, the supply capacitors must be placed as close as possible to the device pins (V_{DD} and GND for the ground-tied supply, V_B and V_S for the floating supply) to minimize parasitic inductance and resistance.

3.2 Gate Drive Loop

Current loops behave like an antenna, able to receive and transmit noise. To reduce the noise coupling/emission and improve the power switch turn-on and off performances, gate drive loops must be reduced as much as possible.

3.3 Ground Plane

Ground plane must not be placed under or nearby the high-voltage floating side to minimize noise coupling.

Mechanical Dimensions

8-SOP

Dimensions are in millimeters (inches) unless otherwise noted.

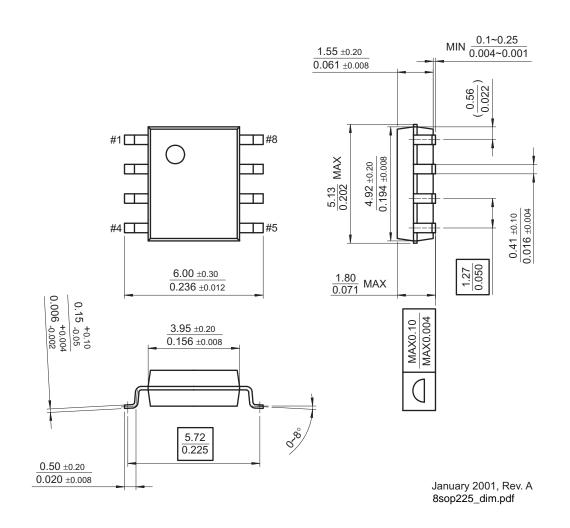
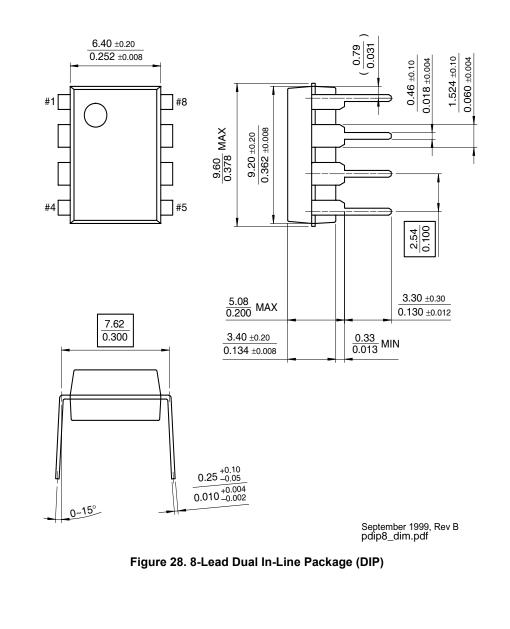


Figure 27. 8-Lead Small Outline Package (SOP)

Mechanical Dimensions (Continued)

8-DIP

Dimensions are in millimeters (inches) unless otherwise noted.





SEMICONDUCTOR

U

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx [®]	HiSeC [™]
Across the board. Around the world. TM	<i>i-Lo</i> ™
ActiveArray TM	Implied
Bottomless TM	IntelliM
Build it Now TM	ISOPL
CoolFET TM	MICRO
$CROSSVOLT^{TM}$	MICRO
CTL TM	MICRO
Current Transfer Logic TM	MSX™
DOME TM	MSXPr
E^2CMOS^{TM}	OCX™
FACT Quiet Series™	OPTOL
FACT [®]	OPTOL
FAST [®]	PACM
FASTr™ FPS™ FRFET [®]	POP™ Power2 Power2 Power8
GlobalOptoisolator™ GTO™	Powers

тм dDisconnect™ /IAX™ ANAR™ OCOUPLER™ Pak™ OWIRE™ ro™ ro™ LOGIC® PLANAR® IAN™ ·220® 247® rEdge™ Saver™

PowerTrench® Programmable Active Droop™ QFET QS™ QT Optoelectronics™ Quiet Series™ RapidConfigure™ RapidConnect™ ScalarPump™ SMART START™ SPM® SuperFET™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 TCM™ The Power Franchise® TinyBoost™ TinyBuck™

TinyLogic[®] TINYOPTO™ TinyPower™ TinyWire™ TruTranslation™ µSerDes™ UHC[®] UniFET™ VCX™ Wire™ FAN73832 Half-Bridge Gate-Drive IC

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary First Production		This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed Full Production		This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only.		

Rev. 123

16